



11-15-02

RCE/1700

Honeywell's Docket No. 30-4790 (4780)  
Practitioner's Docket No. 100595.0048US3

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Zhang, et al.

Application No.: 09/357,264

Group No.: 1765

Filed: July 19, 1999

Examiner: Charlotte A. Brown

For: Composition for Chemical Mechanical Planarization of Copper, Tantalum and Tantalum Nitride

Box RCE

Assistant Commissioner for Patents  
Washington, D.C. 20231

REQUEST FOR CONTINUED EXAMINATION (RCE)  
(37 C.F.R. 1.114)

1. Applicant hereby requests continued examination, in accordance with 37 C.F.R. Section 1.114, for the above identified application.

CERTIFICATION UNDER 37 C.F.R. SECTIONS 1.8(a) AND 1.10  
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## 37 C.F.R. Section 1.8(a)

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## 37 C.F.R. Section 1.10



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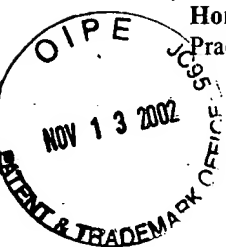
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(Request for Continued Examination (RCE))--page 1 of 3)

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Honeywell's Docket No. 30-4790 (4780)  
Practitioner's Docket No. 100595.0048US3

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**

Serial No: **09/357264**

Filed: **July 19, 1999**

For: **Comp. for Chemical Mechanical  
Planarization of Copper,  
Tantalum and Tantalum Nitride**

Examiner: Brown, Charlotte A.

Art Unit: 1765

PRELIMINARY AMENDMENT

The Honorable Commissioner  
of Patents and Trademarks  
Washington, D.C. 20231

Dear Sir:

IN THE CLAIMS

19. A method of accomplishing chemical mechanical planarization of a Cu/Ta/TaN surface comprising:

providing a single-step slurry solution including a combination selected from the group consisting of (i)  $\text{H}_2\text{O}_2$  with  $\text{H}_3\text{PO}_4$ ,  $\text{H}_2\text{SO}_4$ ,  $\text{HNO}_3$ , oxalic acid, acetic acid, or organic acid, (ii)  $\text{HNO}_3$  with  $\text{H}_3\text{PO}_4$ , or  $\text{H}_2\text{SO}_4$ ; and (iii) an oxidizing reagent with HF;

applying the solution to the surface; and

planarizing both the Cu and at least one of the Ta and TaN during a single processing step.

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